



Stacked bare AlN ceramic substrates

Aluminum Nitride Substrates for Thick-Film Circuits

Product ID / SKU: FWM/CS-ALN-002

Material: Aluminum Nitride

Product type: Ceramic Substrate

AlN substrates prepared for thick-film circuit processing where thermal management and electrical insulation are required.

95% AlN Substrate Properties

Property	95% AlN typical value	Condition / method
AlN content (%)	95	-
Density (g/cm ³)	≥3.3	-
Flexural strength (MPa)	≥400	-
Thermal conductivity (W/(m·K))	≥170	Room temperature
Relative permittivity	8-10	1 MHz; room temperature
Dielectric loss tangent	≤0.0003	1 MHz; room temperature
Dielectric strength (kV/mm)	17	-
Volume resistivity (Ω·cm)	≥10 ¹⁴	-